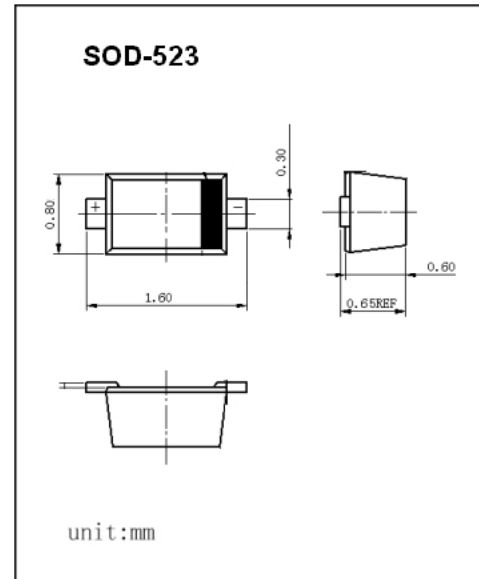




## RB751S-40 Schottky barrier Diodes

### FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability



### Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	40	V
DC reverse voltage	V <sub>R</sub>	30	V
Mean rectifying current	I <sub>O</sub>	30	mA
Peak forward surge current	I <sub>FSM</sub>	200	mA
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55~+125	°C

### Electrical Ratings @T<sub>A</sub>=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>			0.37	V	I <sub>F</sub> =1mA
Reverse current	I <sub>R</sub>			0.5	μA	V <sub>R</sub> =30V
Capacitance between terminals	C <sub>T</sub>		2		pF	V <sub>R</sub> =1V, f=1MHZ

# Typical Characteristics

# RB751S-40

## ●Electrical characteristic curves (Ta = 25°C)

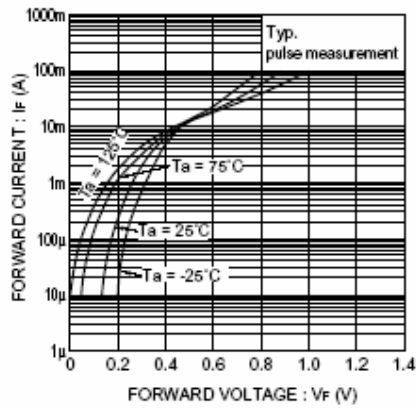


Fig. 1 Forward characteristics

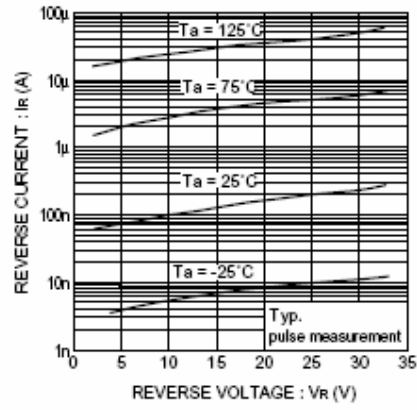


Fig. 2 Reverse characteristics

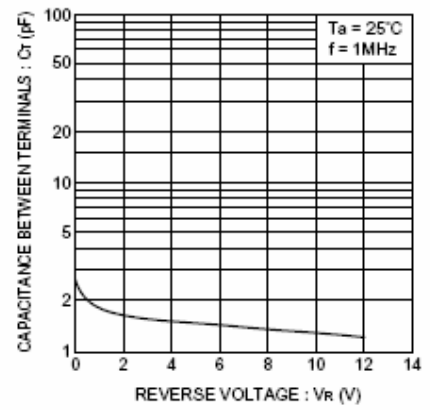


Fig. 3 Capacitance between terminals characteristics